

MSCSM120AM042CD3AG
Datasheet
Phase Leg SiC Power Module

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a  **MICROCHIP** company

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1 Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

1.1 Revision 1.0

Revision 1.0 is the first publication of this document, published in January 2020.

2 Product Overview

The MSCSM120AM042CD3AG is a phase leg 1200 V/495 A silicon carbide power module.

Figure 1 • MSCSM120AM042CD3AG Electrical Schematic

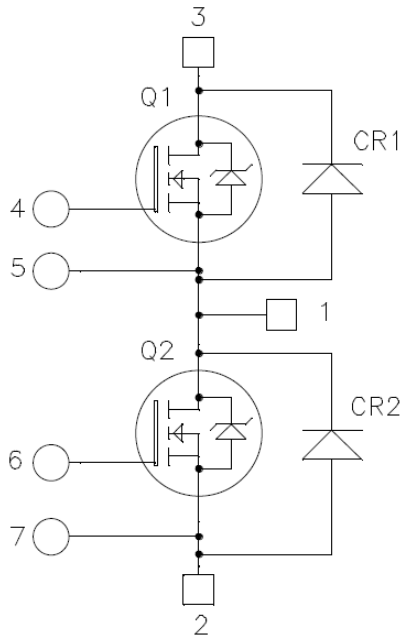
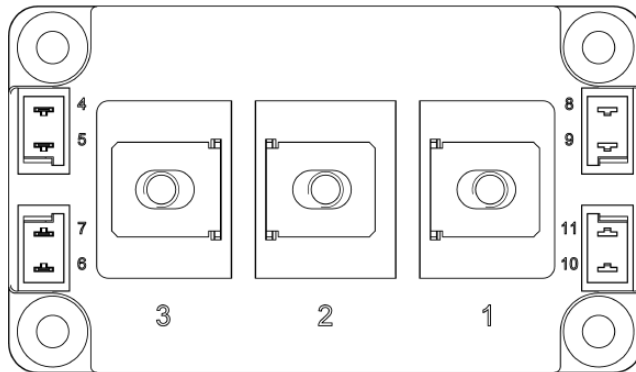


Figure 2 • MSCSM120AM042CD3AG Pinout Location



All ratings at $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.

2.1 Features

The following are key features of the MSCSM120AM042CD3AG device:

- SiC Power MOSFET
 - Low RDS(on)
 - High temperature performance
- Silicon carbide (SiC) Schottky diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature-independent switching behavior
 - Positive temperature coefficient on VF
- Kelvin emitter for easy drive
- High level of integration
- Aluminum nitride (AlN) substrate for improved thermal performance
- M6 power connectors

2.2 Benefits

The following are benefits of the MSCSM120AM042CD3AG device:

- High efficiency converters
- Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- RoHS Compliant

2.3 Applications

The MSCSM120AM042CD3AG device is designed for the following applications:

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- EV motor and traction drive

3 Electrical Specifications

This section shows the electrical specifications of the MSCSM120AM042CD3AG device.

3.1 SiC MOSFET Characteristics (Per MOSFET)

This section describes the electrical characteristics of the MSCSM120AM042CD3AG device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Maximum Ratings	Unit
V_{DSS}	Drain-source voltage	1200	V
I_D	Continuous drain current	$T_C = 25\text{ }^\circ\text{C}$ 495 ¹	A
		$T_C = 80\text{ }^\circ\text{C}$ 395 ¹	
I_{DM}	Pulsed drain current	990	
V_{GS}	Gate-source voltage	-10/25	V
R_{Dson}	Drain-source ON resistance	5.2	m Ω
P_D	Power dissipation	$T_C = 25\text{ }^\circ\text{C}$ 2031	W

Note:

1. Specification of SiC MOSFET device but output current must be limited due to the size of power connectors.

Table 2 • Electrical Characteristics

Sym- bol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}; V_{DS} = 1200\text{ V}$		60	600	μA
R_{Dson}	Drain-source on resistance	$V_{GS} = 20\text{ V}$ $I_D = 240\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	4.2	5.2	m Ω
			$T_J = 175\text{ }^\circ\text{C}$	6.7		
$V_{GS(th)}$	Gate threshold voltage	$V_{GS} = V_{DS}, I_D = 6\text{ mA}$	1.8	2.8		V
I_{GSS}	Gate-source leakage current	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			600	nA

Table 3 • Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}$		18.1		pF
C_{oss}	Output capacitance	$V_{DS} = 1000\text{ V}$ $f = 1\text{ MHz}$		1.6		
C_{rss}	Reverse transfer capacitance			0.15		
Q_g	Total gate charge	$V_{GS} = -5/20\text{ V}$		1392		nC
Q_{gs}	Gate–source charge	$V_{Bus} = 800\text{ V}$ $I_D = 240\text{ A}$		246		
Q_{gd}	Gate–drain charge			300		
$T_{d(on)}$	Turn-on delay time	$V_{GS} = -5/20\text{ V}$		56		ns
T_r	Rise time	$V_{Bus} = 600\text{ V}$ $I_D = 300\text{ A}$		55		
$T_{d(off)}$	Turn-off delay time	$R_{Gon} = 1.3\Omega$; $R_{Goff} = 0.8\Omega$ $T_J = 150\text{ }^\circ\text{C}$		166		
T_f	Fall time			67		
E_{on}	Turn on energy	Inductive Switching $V_{GS} = -5/20\text{ V}$	$T_J = 150\text{ }^\circ\text{C}$	6.1		mJ
E_{off}	Turn off energy	$V_{Bus} = 600\text{ V}$ $I_D = 300\text{ A}$ $R_{Gon} = 1.3\Omega$ $R_{Goff} = 0.8\Omega$	$T_J = 150\text{ }^\circ\text{C}$	5.5		mJ
R_{Gint}	Internal gate resistance			1		Ω
R_{thJC}	Junction-to-case thermal resistance				0.074	$^\circ\text{C/W}$

Table 4 • Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{SD}	Diode forward voltage	$V_{GS} = 0\text{ V}$; $I_{SD} = 240\text{ A}$		4		V
		$V_{GS} = -5\text{ V}$; $I_{SD} = 240\text{ A}$		4.2		
t_{rr}	Reverse recovery time	$I_{SD} = 240\text{ A}$; $V_{GS} = -5\text{ V}$; $V_R = 800\text{ V}$; $diF/dt = 6000\text{ A}/\mu\text{s}$		90		ns
Q_{rr}	Reverse recovery charge			3300		nC
I_{rr}	Reverse recovery current			81		A

3.2 SiC Schottky Diode Ratings Characteristics (Per SiC Diode)

This section shows the SiC Schottky diode ratings and characteristics of the device.

Table 5 • SiC Schottky Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Peak repetitive reverse voltage				1200	V
I_{RRM}	Reverse leakage current	$V_R = 1200\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$	60	1200	μA
			$T_J = 175\text{ }^\circ\text{C}$	900		
I_F	Forward current		$T_C = 100\text{ }^\circ\text{C}$	180		A
V_F	Diode forward voltage	$I_F = 180\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	1.5	1.8	V
			$T_J = 175\text{ }^\circ\text{C}$	2.1		
Q_C	Total capacitive charge	$V_R = 600\text{ V}$		780		nC
C	Total capacitance	$f = 1\text{ MHz}, V_R = 400\text{ V}$		846		μF
		$f = 1\text{ MHz}, V_R = 800\text{ V}$		630		
R_{thJC}	Junction-to-case thermal resistance				0.175	$^\circ\text{C/W}$

3.3 Thermal Package Characteristics

This section shows the thermal and package characteristics of the device.

Table 6 • Package Characteristics

Symbol	Characteristic		Min	Max	Unit	
V_{ISOL}	RMS isolation voltage, any terminal to case $t = 1\text{ min}, 50/60\text{ Hz}$		4000		V	
T_J	Operating junction temperature range		-40	175	$^\circ\text{C}$	
T_{JOP}	Recommended junction temperature under switching conditions		-40	$T_{Jmax} - 25$	$^\circ\text{C}$	
T_{STG}	Storage temperature range		-40	125	$^\circ\text{C}$	
T_C	Operating case temperature		-40	125	$^\circ\text{C}$	
Torque	Mounting torque	For terminals	M6	3	5	N.m
		To heatsink	M6	3	5	
Wt	Package weight			350	g	

3.4 Typical SiC MOSFET Performance Curves

This section shows the typical performance curves of the MSCSM120AM042CD3AG SiC MOSFET.

Figure 3 • Maximum Thermal Impedance

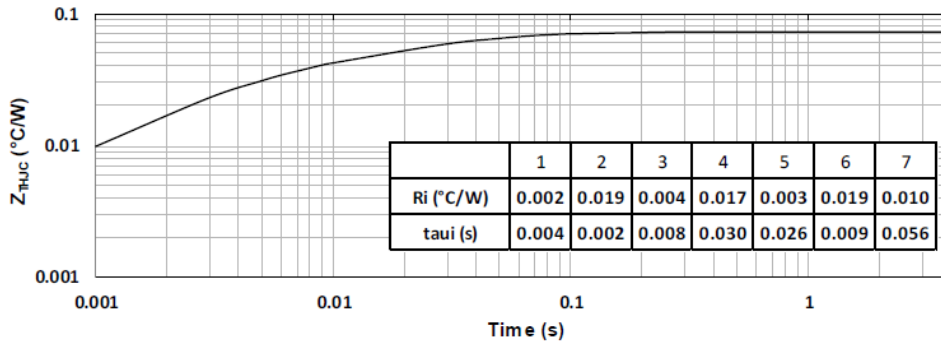


Figure 4 • Output Characteristics, T_J = 25 °C

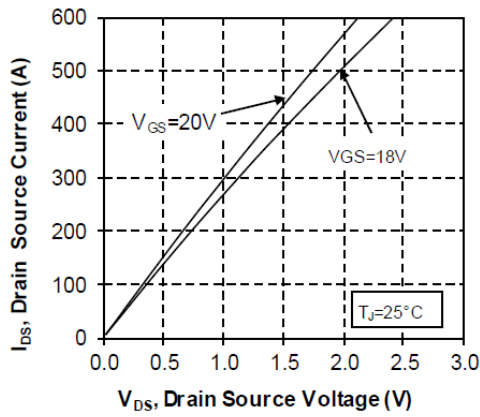


Figure 5 • Output Characteristics, T_J = 175 °C

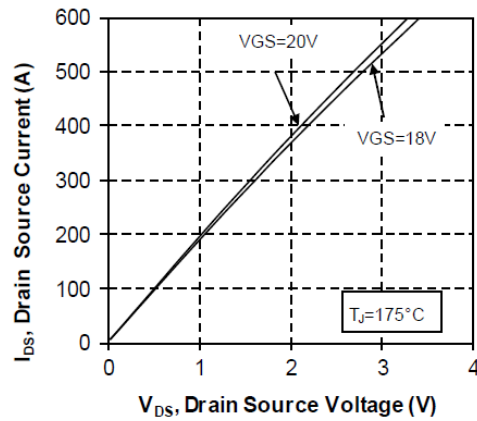


Figure 6 • Normalized RDS(on) vs. Temperature

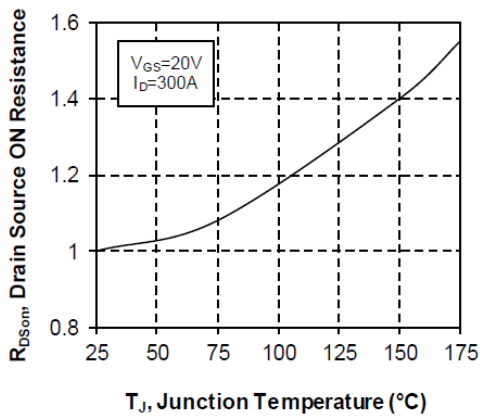


Figure 7 • Transfer Characteristics

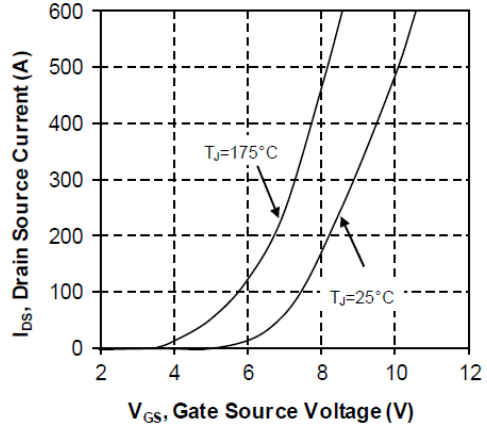


Figure 8 • Switching Energy vs. Rg

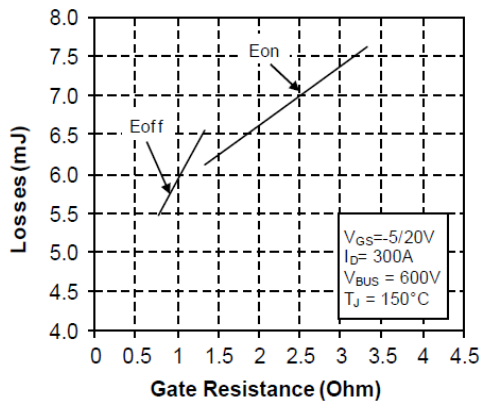


Figure 9 • Switching Energy vs. Current

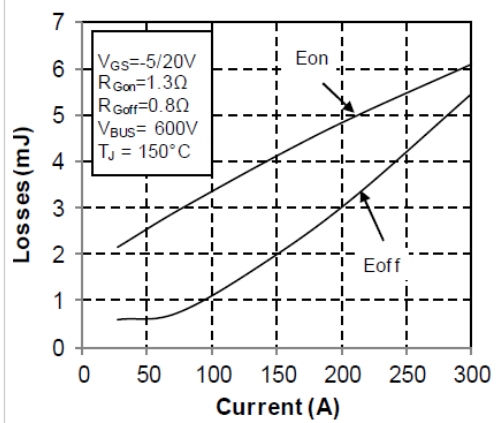


Figure 10 • Capacitance vs. Drain Source Voltage

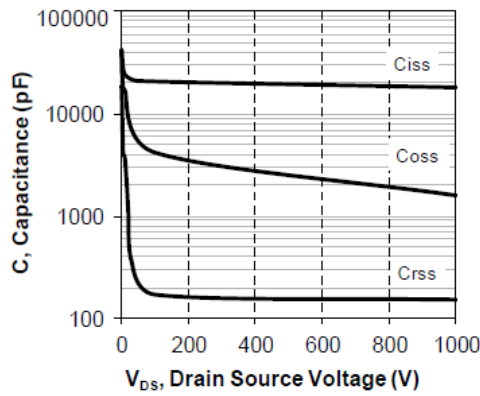


Figure 11 • Gate Charge vs. Gate Source Voltage

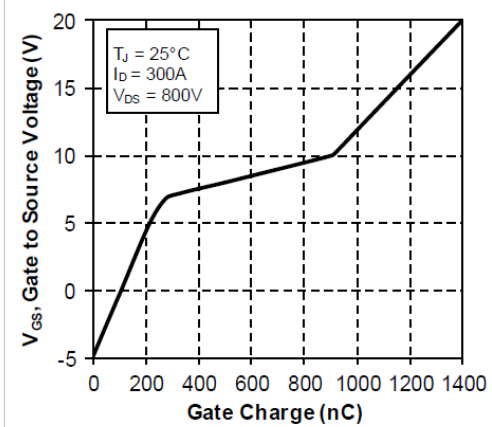


Figure 12 • Body Diode Characteristics, TJ = 25 °C

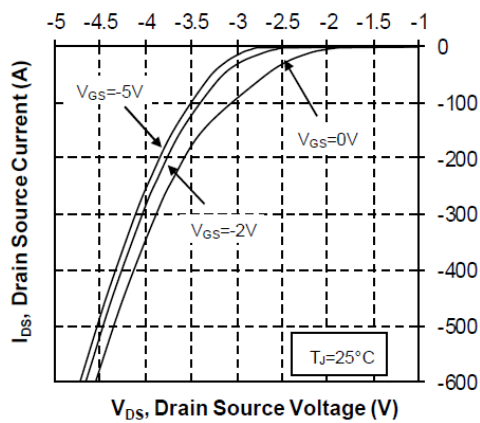


Figure 13 • 3rd Quadrant Characteristics, TJ = 25 °C

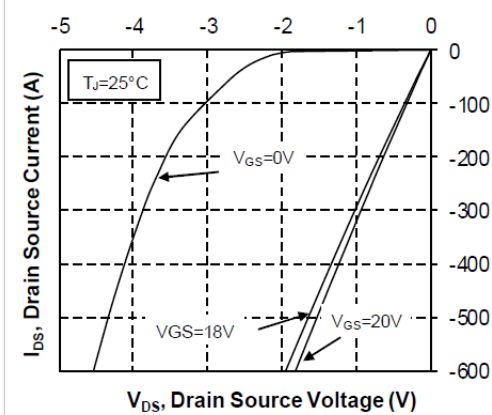


Figure 14 • Body Diode Characteristics, $T_J = 175^\circ\text{C}$

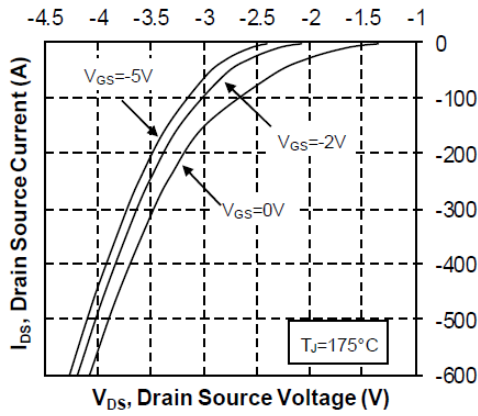


Figure 15 • 3rd Quadrant Characteristics, $T_J = 175^\circ\text{C}$

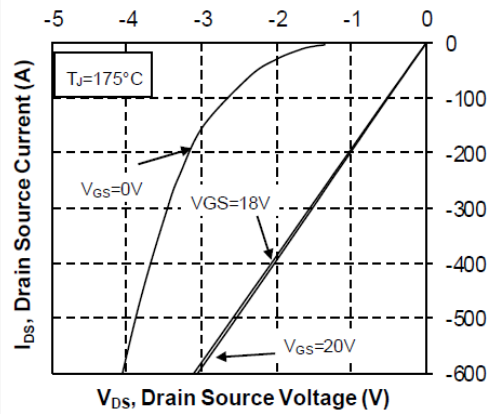
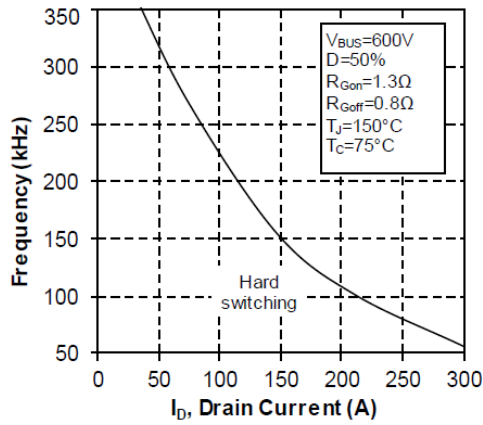


Figure 16 • Operating Frequency vs. Drain Current



3.5 Typical SiC Diode Performance Curves

This section shows the typical performance curves of the MSCSM120AM042CD3AG SiC diode.

Figure 17 • Maximum Thermal Impedance

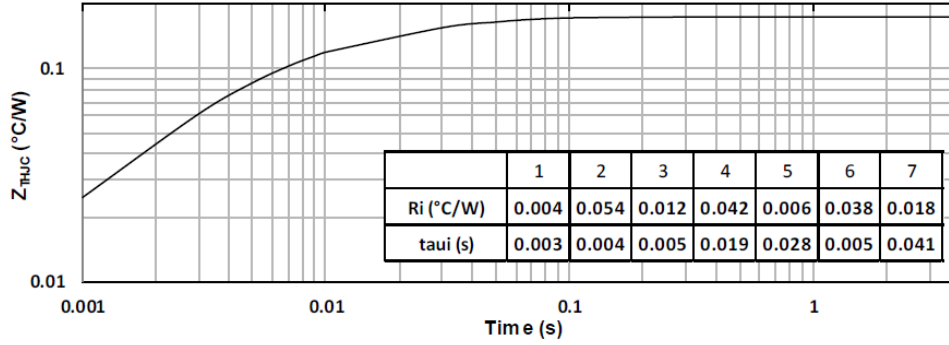


Figure 18 • Forward Characteristics

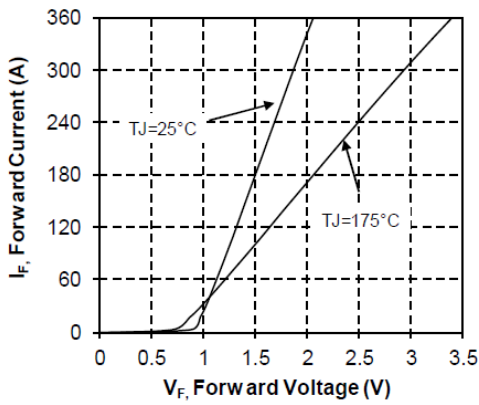
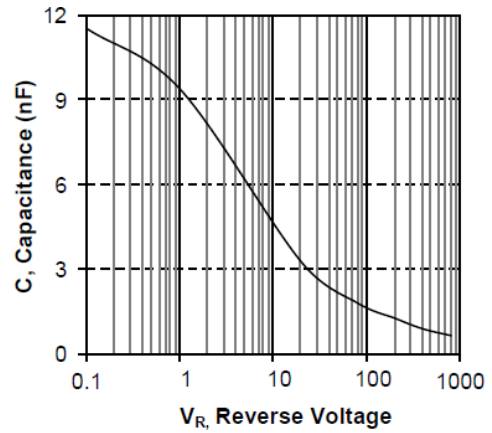


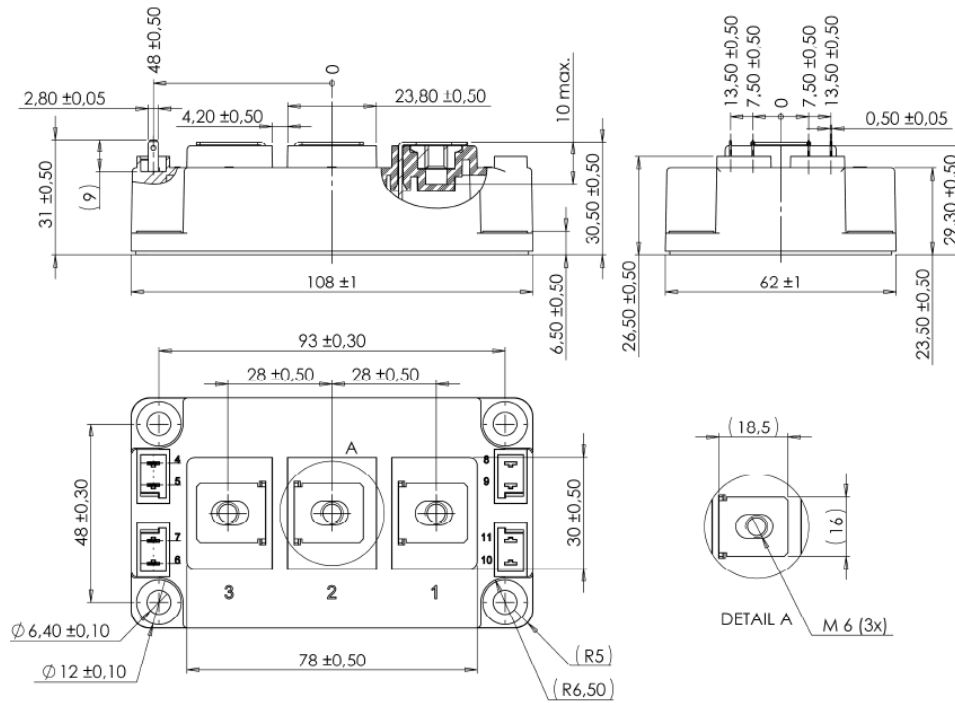
Figure 19 • Capacitance vs. Reverse Voltage



4 Package Specifications

This section shows the package outline of the MSCSM120AM042CD3AG device. All dimensions are in millimeters.

Figure 20 • Package Outline



See application note 1908 - Mounting instructions for D3 and D4 power modules on www.microsemi.com